



(12) **Patent Application Publication**
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(43) **Pub. Date:** **Jun. 27, 2024**

(52) U.S. Cl.

CPC *H01L 23/49894* (2013.01); *H01L 23/147* (2013.01); *H01L 23/49822* (2013.01); *H01L 23/49838* (2013.01); *H01L 24/16* (2013.01); *H01L 24/29* (2013.01); *H01L 24/32* (2013.01); *H01L 24/73* (2013.01); *H01L 2224/16227* (2013.01); *H01L 2224/16238* (2013.01); *H01L 2224/29186* (2013.01); *H01L 2224/29686* (2013.01); *H01L 2224/32225* (2013.01); *H01L 2224/73204* (2013.01); *H01L 2924/01014* (2013.01); *H01L 2924/35121* (2013.01)

(57) **ABSTRACT**

A semiconductor package includes a first substrate including silicon, a first insulating layer in contact with the first substrate, the first insulating layer including silicon oxide, the first insulating layer having a first concentration of silicon, a second insulating layer in contact with the first insulating layer, the second insulating layer including silicon oxide, the second insulating layer having a second concentration of silicon, the second concentration lower than the first concentration, and a structure on the second insulating layer. The first concentration is a ratio of a weight of silicon in the first insulating layer to a total weight of the first insulating layer, the second concentration is a ratio of a weight of silicon in the second insulating layer to a total weight of the second insulating layer, and the first concentration is in a range from 20 wt % to 50 wt %.

(22) Filed: **Nov. 30, 2023**

(30) **Foreign Application Priority Data**

Dec. 22, 2022 (KR) 10-2022-0181439

Publication Classification

(51) **Int. Cl.**

H01L 23/498 (2006.01)

H01L 23/00 (2006.01)

H01L 23/14 (2006.01)

